

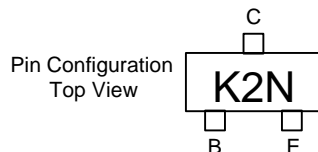


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MMST3904

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type available (MMST3906)
- Ultra-small surface mount package
- Marking Code: K2N



Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current-Continuous ⁽¹⁾	200	mA
P_C	Power dissipation ⁽¹⁾	200	mW
T_J	Junction Temperature	-55 to +150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS⁽²⁾

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=1.0mA$, $I_B=0$)	40	---	Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=10\mu A$, $I_E=0$)	60	---	Vdc
$V_{(BR)EBO}$	Collector-Emitter Breakdown Voltage ($I_C=10\mu A$, $I_C=0$)	5.0	---	Vdc
I_{CEX}	Collector-Base Cutoff Current ($V_{CE}=30Vdc$, $V_{EB(OFF)}=3.0Vdc$)	---	50	nAdc
I_{EL}	Emitter-Base Cutoff Current ($V_{CE}=30Vdc$, $V_{EB(OFF)}=3.0Vdc$)	---	50	nAdc

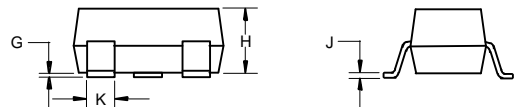
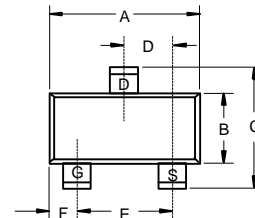
ON CHARACTERISTICS⁽²⁾

h_{FE}	DC Current Gain ($I_C=100\mu A$, $V_{CE}=1.0Vdc$) ($I_C=1.0mA$, $V_{CE}=1.0Vdc$) ($I_C=10mA$, $V_{CE}=1.0Vdc$) ($I_C=50mA$, $V_{CE}=1.0Vdc$) ($I_C=500mA$, $V_{CE}=1.0Vdc$)	40 70 100 60 30	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=10mA$, $I_B=1.0mA$) ($I_C=50mA$, $I_B=5.0mA$)	---	0.25 0.30	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=10mA$, $I_B=1.0mA$) ($I_C=50mA$, $I_B=5.0mA$)	0.65 ---	0.85 0.95	Vdc

Note: 1. Valid provided that terminals are kept at ambient temperature.
2. Pulse test: Pulse width<300us, duty cycle<2%

NPN Small Signal Transistors

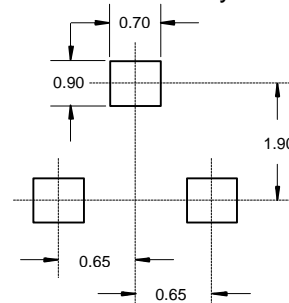
SOT-323



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.071	.087	1.80	2.20	
B	.045	.053	1.15	1.35	
C	.079	.087	2.00	2.20	
D	.026 Nominal		0.65Nominal		
E	.047	.055	1.20	1.40	
F	.012	.016	.30	.40	
G	.000	.004	.000	.100	
H	.035	.039	.90	1.00	
J	.004	.010	.100	.250	
K	.012	.016	.30	.40	

Suggested Solder Pad Layout



MMST3904



SMALL SIGNAL CHARACTERISTICS

C_{obo}	Output Capacitance ($V_{CB}=5.0Vdc, f=1.0MHz, I_E=0$)	---	4.0	pF	
C_{ibo}	Input Capacitance ($V_{EB}=0.5Vdc, f=1.0MHz, I_C=0$)	---	8.0	pF	
h_{ie}	Input Impedance	$V_{CE}=10Vdc, I_C=1.0mA, f=1.0KHz$	1.0	10	kohms
h_{re}	Voltage Feedback Ratio		0.5	8.0	$\times 10^{-4}$
h_{fe}	Small Signal Current Gain		100	400	---
h_{oe}	Output Admittance		1.0	40	μS
f_T	Current Gain-Bandwidth Product ($V_{CE}=20Vdc, I_C=10mA, f=100MHz$)	300	---	NHz	
NF	Noise Figure ($V_{CE}=5.0Vdc, I_C=100\mu A, R_S=1.0KOHMS, f=1.0KHz$)	---	5.0	dB	

SWITCHING CHARACTERISTICS

t_d	Delay Time	$V_{CC}=3.0Vdc, I_B=100\mu A,$	---	35	ns
t_r	Rise Time	$V_{BE(off)}=0.5Vdc, I_B=1.0mA$	---	35	ns